

R-C Thermal Model Parameters

DESCRIPTION

The parametric values in the R-C thermal model have been derived using curve-fitting techniques. These techniques are described in "[A Simple Method of Generating Thermal Models for a Power MOSFET](#)"[1]. When implemented in P-Spice, these values have matching characteristic curves to the Single Pulse Transient Thermal Impedance curves for the MOSFET.

R-C values for the electrical circuit in the Foster/Tank and Cauer/Filter configurations are included.

Note:

For a detailed explanation of implementing these values in P-SPICE, refer to [Application Note AN609 Thermal Simulations Of Power MOSFETs on P-SPICE Platform](#).

R-C THERMAL MODEL FOR TANK CONFIGURATION



R-C VALUES FOR TANK CONFIGURATION					
Thermal Resistance (°C/W)					
Junction to	Ambient Nch	Ambient Pch	Foot	Case Nch	Case Pch
RT1	5.0788	5.0788	N/A	1.7033	1.7033
RT2	11.4296	11.4296	N/A	1.0356	1.0356
RT3	13.1479	13.1479	N/A	908.5000 m	908.5000 m
RT4	55.3437	55.3437	N/A	1.8526	1.8526
Thermal Capacitance (Joules/°C)					
Junction to	Ambient Nch	Ambient Pch	Foot	Case Nch	Case Pch
CT1	916.4415 u	916.4415 u	N/A	10.4943 m	10.4943 m
CT2	18.3715 m	18.3715 m	N/A	1.8989 m	1.8989 m
CT3	255.3144 m	255.3144 m	N/A	338.9567 m	338.9567 m
CT4	1.3848	1.3848	N/A	869.8553 u	869.8553 u

This document is intended as a SPICE modeling guideline and does not constitute a commercial product data sheet. Designers should refer to the appropriate data sheet of the same number for guaranteed specification limits.

R-C THERMAL MODEL FOR FILTER CONFIGURATION**R-C VALUES FOR FILTER CONFIGURATION**

Thermal Resistance ($^{\circ}\text{C}/\text{W}$)					
Junction to	Ambient Nch	Ambient Pch	Foot	Case Nch	Case Pch
RF1	5.3819	5.3819	N/A	3.0847	3.0847
RF2	11.6351	11.6351	N/A	1.6725	1.6725
RF3	15.8984	15.8984	N/A	634.7250 m	634.7250 m
RF4	52.0846	52.0846	N/A	108.0750 m	108.0750 m
Thermal Capacitance (Joules/ $^{\circ}\text{C}$)					
Junction to	Ambient Nch	Ambient Pch	Foot	Case Nch	Case Pch
CF1	842.4869 u	842.4869 u	N/A	552.0837 u	552.0837 u
CF2	14.1484 m	14.1484 m	N/A	9.4244 m	9.4244 m
CF3	166.5741 m	166.5741 m	N/A	581.8856 m	581.8856 m
CF4	1.2308	1.2308	N/A	2.0847 m	2.0847 m

Note: NA indicates not applicable

Reference:

[1] "A Simple Method of Generating Thermal Models for a Power MOSFET" by Wharton McDaniel and Kandarp Pandya. IEEE / SEMITHERM 2002



